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2. (Amended) The dielectric substrates, as recited in claim 1, further comprising:
said dielectric substrates being heated for at least 20 hours at between 1400° C and 1600 °

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said dielectric substrates having a low dielectric constant in the range of 4.1 to 16.3; and
said dielectric substrates having a low dielectric loss in the range of less than 1×10^{-3} to 9×10^{-3} without a phase transition.

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4. (Twice Amended) The dielectric substrate, according to claim 3, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite cubic crystalline structure;
said dielectric substrate having a low dielectric constant of 15.1; and
said dielectric substrate having a low dielectric loss of less than 1×10^{-3} .

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7. (Twice Amended) The dielectric substrate, according to claim 6, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline
structure;
20 said dielectric substrate having a low dielectric constant of 5.1; and
said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

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25 10. (Twice Amended) The dielectric substrate, according to claim 9, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline
structure;
said dielectric substrate having a low dielectric constant of 10.0; and
said dielectric substrate having a low dielectric loss of 2.0×10^{-3} .

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13. (Twice Amended) The dielectric substrate, according to claim 12, further comprising:

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said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline structure;
said dielectric substrate having a low dielectric constant of 5.3; and
said dielectric substrate having a low dielectric loss of 1.6×10^{-3} .

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16. (Twice Amended) The dielectric substrate, according to claim 15, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline structure;
said dielectric substrate having a low dielectric constant of 11.6; and
said dielectric substrate having a low dielectric loss of about 3.1×10^{-3} .

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19. (Twice Amended) The dielectric substrate, according to claim 18, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline structure;
said dielectric substrate having a low dielectric constant of 11.2; and
said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

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22. (Twice Amended) The dielectric substrate, according to claim 21, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline structure;
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said dielectric substrate having a low dielectric constant of 12.9; and
said dielectric substrate having a low dielectric loss of 1.4×10^{-3} .

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25. (Twice Amended) The dielectric substrate, according to claim 24, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline

structure;

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said dielectric substrate having a low dielectric constant of 7.1; and
said dielectric substrate having a low dielectric loss of 1.4×10^{-3} .

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28. (Twice Amended) The dielectric substrate, according to claim 27, further comprising:
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said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite cubic crystalline structure;
said dielectric substrate having a low dielectric constant of 16.3; and
said dielectric substrate having a low dielectric loss of 3.8×10^{-3} .

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31. (Twice Amended) The dielectric substrate, according to claim 30, further comprising:
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said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline
structure;

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said dielectric substrate having a low dielectric constant of 12.1; and
said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

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34. (Twice Amended) The dielectric substrate, according to claim 33, further comprising:
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said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline
structure;
said dielectric substrate having a low dielectric constant of 13.6; and
said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

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37. (Twice Amended) The dielectric substrate, according to claim 36, further comprising:
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said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline
structure;
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said dielectric substrate having a low dielectric constant of 10.9; and
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said dielectric substrate having a low dielectric loss of 2.2×10^{-3} .